

# IDS LIST OF REFERENCES UNDER 37 C.F.R. 1.98

Sheet 1 of 2

Application Number : 10/595,523  
 Filing Date : April 25, 2006  
 First Named Inventor : Masahiro Nakayama  
 Art Unit : 2895  
 Examiner Name : Jae Lee  
 Docket Number : 039.0071

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T
	F1	JP-2003-101068-A	04-04-2003	Sanyo Electric		<input type="checkbox"/>

Examiner Signature	/Jae Lee/	Date Considered	12/14/2009
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**NON PATENT DOCUMENTS**

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
	01	M. LESZCZYNSKI et al., "GaN Homoepitaxial Layers Grown by Metalorganic Chemical Vapor Deposition," Applied Physics Letters, August 30, 1999, pp. 1276-1278, Vol. 75, No. 9, American Institute of Physics, NY.	<input type="checkbox"/>

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